

What is claimed is:

1. A method of removing photoresist from a wafer having a front surface, a side surface, and a rear surface, said method comprising:

transferring the wafer into a process chamber;

positioning the wafer on an upper surface of a wafer stage within said process chamber;

heating the wafer positioned on the upper surface of the wafer stage to a temperature between 210°C to 230°C using a heater disposed within the stage;

raising the heated wafer above the upper surface of the wafer stage to expose the bottom surface of the wafer; and

after the wafer has been transferred into the process chamber, only producing plasma in the process chamber once the heated wafer has been raised above the upper surface of the wafer stage, such that the plasma removes any photoresist all at the same time from the front, side and rear surfaces of the wafer.

2. The method according to claim 1, wherein said raising the heated wafer comprises spacing the wafer a distance of 9 mm to 11 mm above the upper surface of the wafer stage, and wherein the plasma is produced only once the wafer is at said distance above the upper surface of the wafer stage.